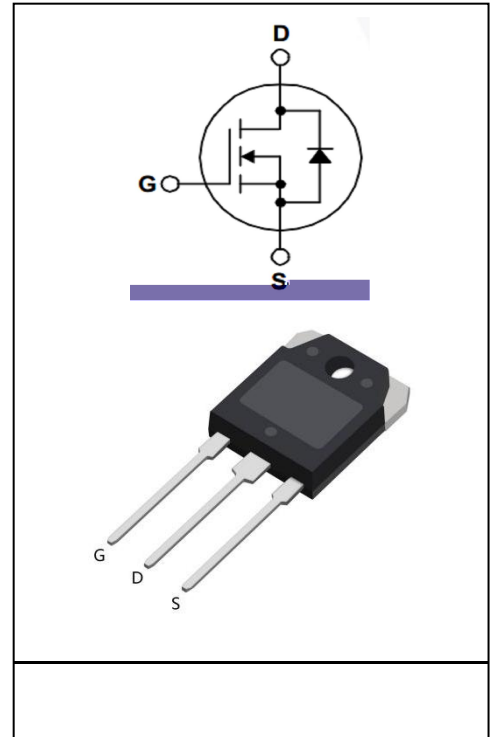


A



- A
- 
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A

	A

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- A

Drain-source voltage	$V_{DS}$	300	V
Continuous drain current $T_C = 25^\circ\text{C}$ (Silicon limit)	$I_D$	59	A
Pulsed drain current ( $T_C = 25^\circ\text{C}$ , $t_p$ limited by $T_{jmax}$ )	$I_{DM}$	236	A
Avalanche energy, single pulse ( $L=10\text{mH}$ , $R_g=25\ \Omega$ )	$E_{AS}$	2419	mJ
Gate-Source voltage	$V_{GS}$	$\pm 30$	V
Power dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	480	W
Operating junction and storage temperature		-55...+150	$^\circ\text{C}$

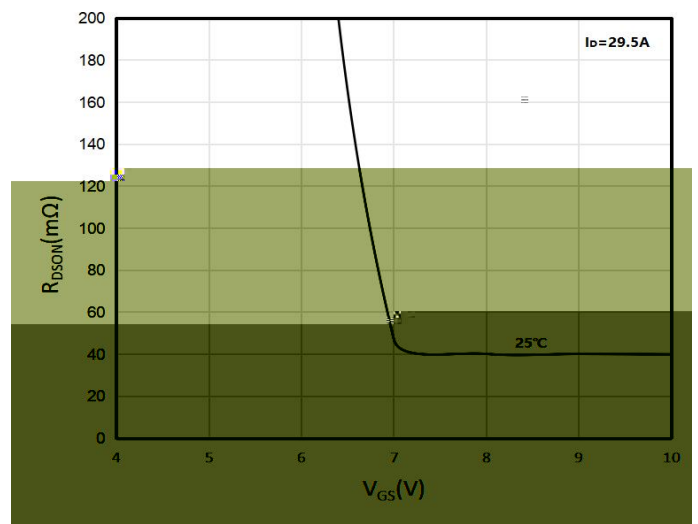
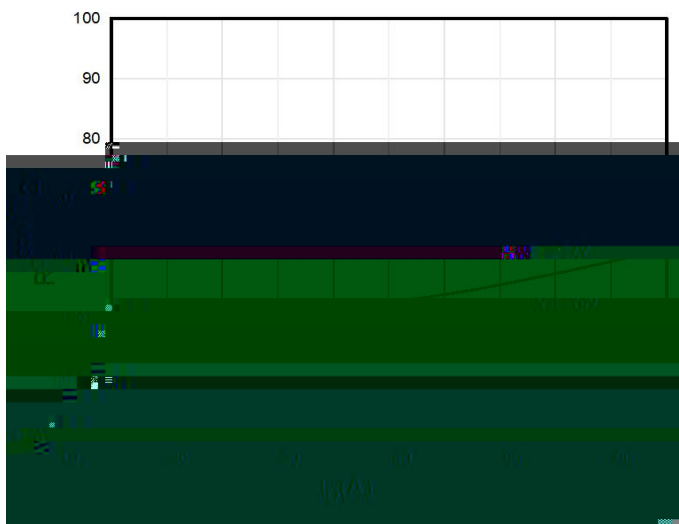
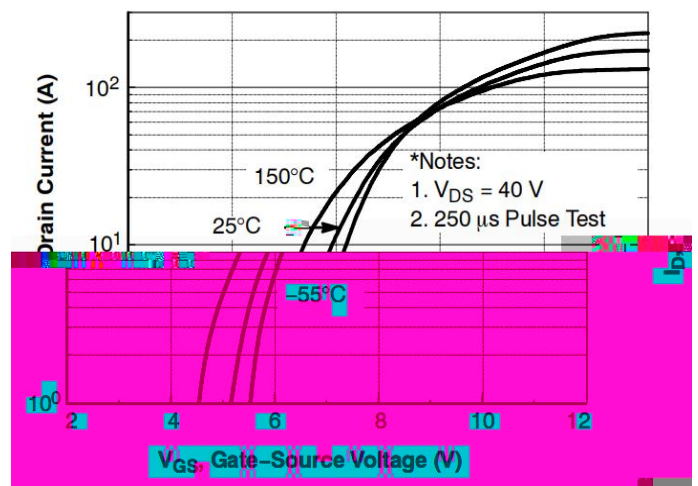
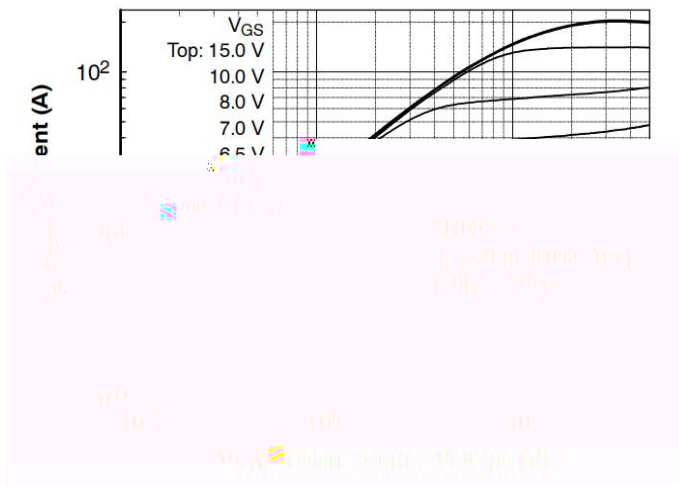
Thermal resistance, junction – case.	$R_{thJC}$	0.26	/W
Thermal resistance, junction – ambient(min. footprint)	$R_{thJA}$	40	

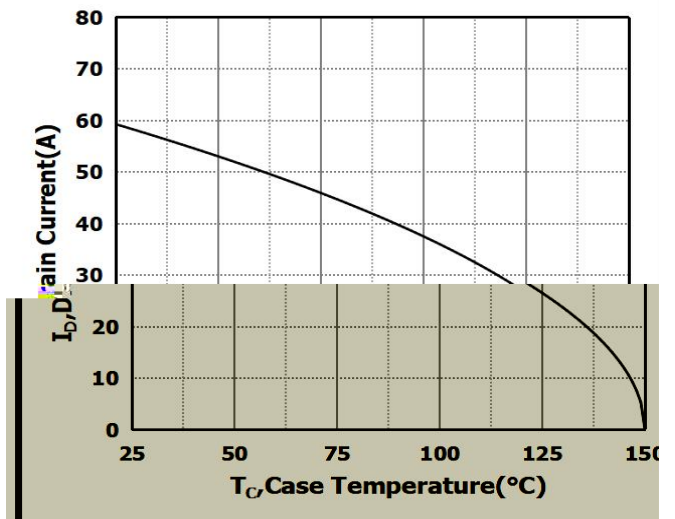
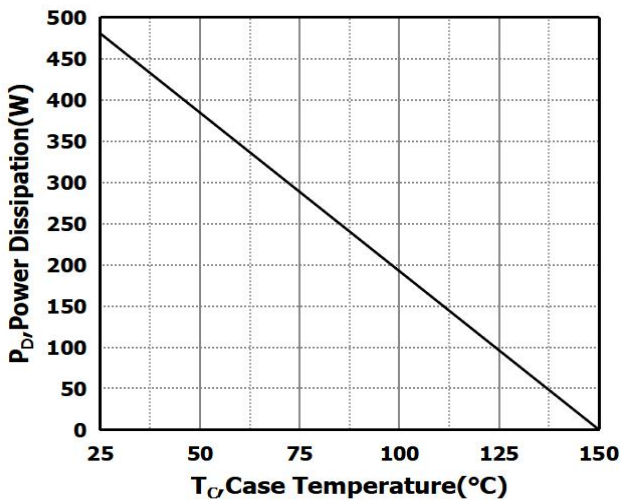
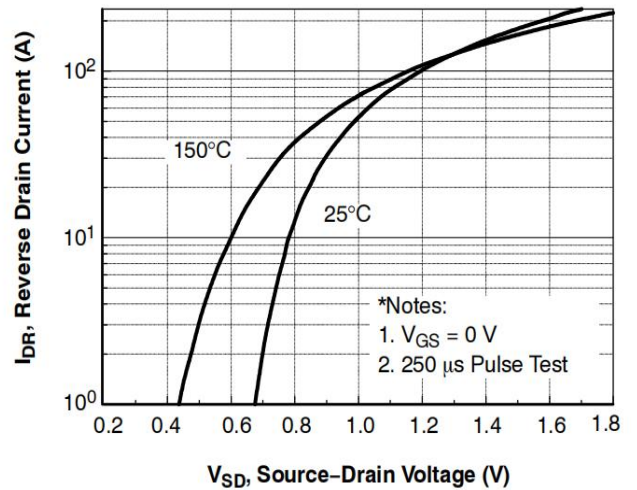
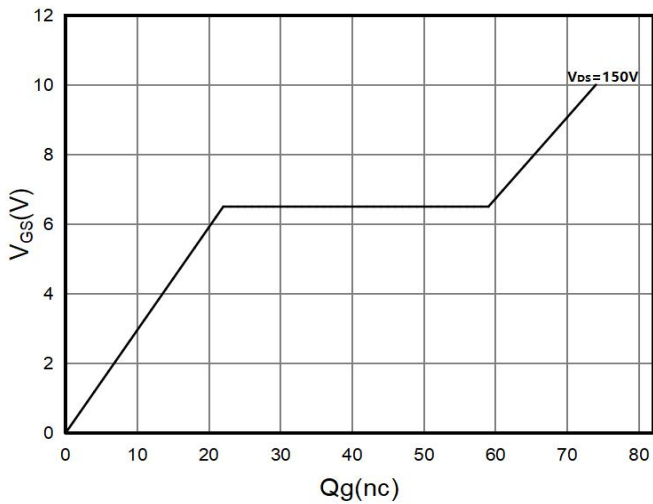
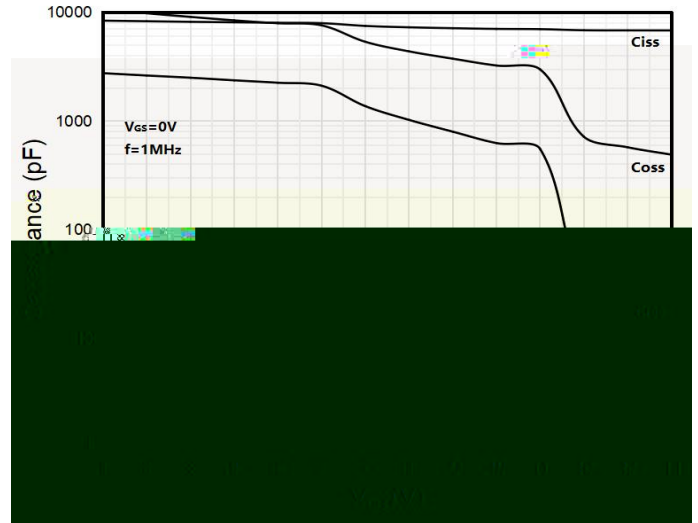
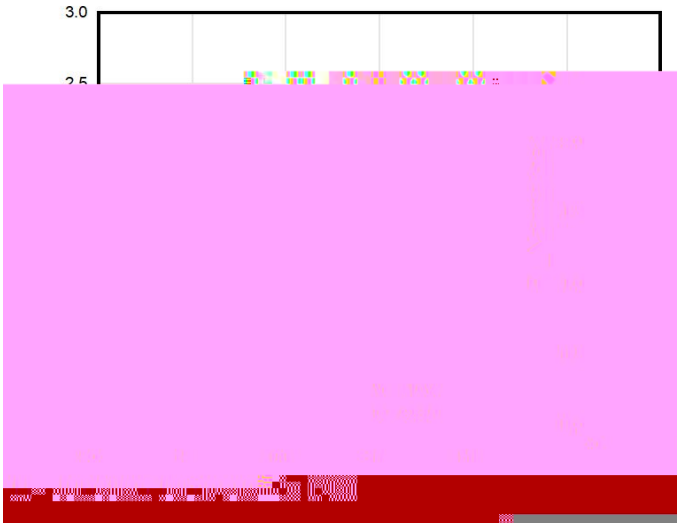
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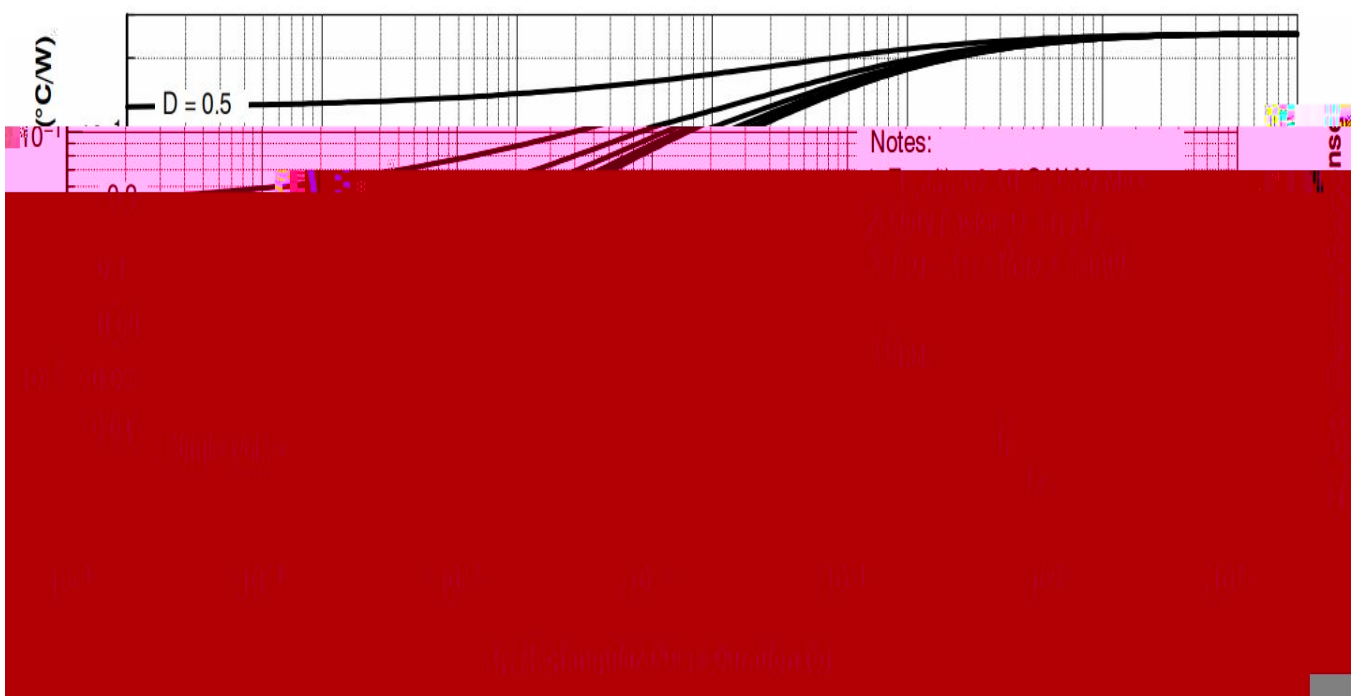
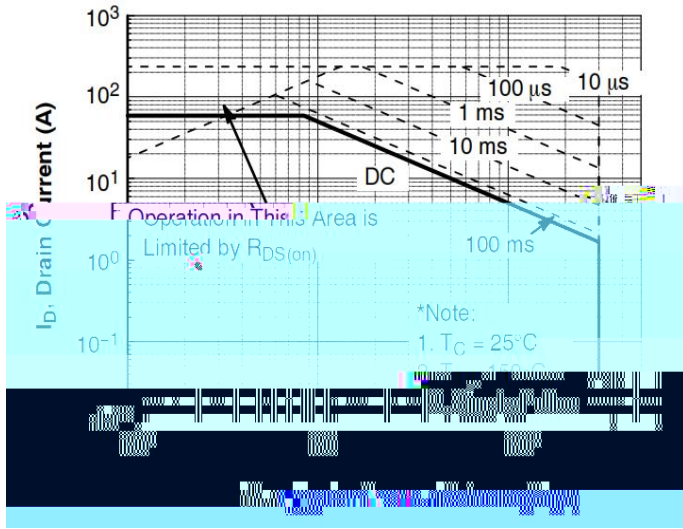
Drain-source breakdown voltage	$BV_{DSS}$	300	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	2.0	-	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu A$	$V_{DS}=300V, V_{GS}=0V$ $T_j=25$
		-	-	10	$\mu A$	$V_{DS}=240V, V_{GS}=0V$ $T_j=125$
Gate-source leakage current	$I_{GSS}$	-	-	$\pm 100$	nA	$V_{GS}=\pm 30V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	47	57	m	$V_{GS}=10V, I_D=29.5A$
Transconductance	$g_{fs}$	-	52	-	S	$V_{DS}=40V, I_D=29.5A$

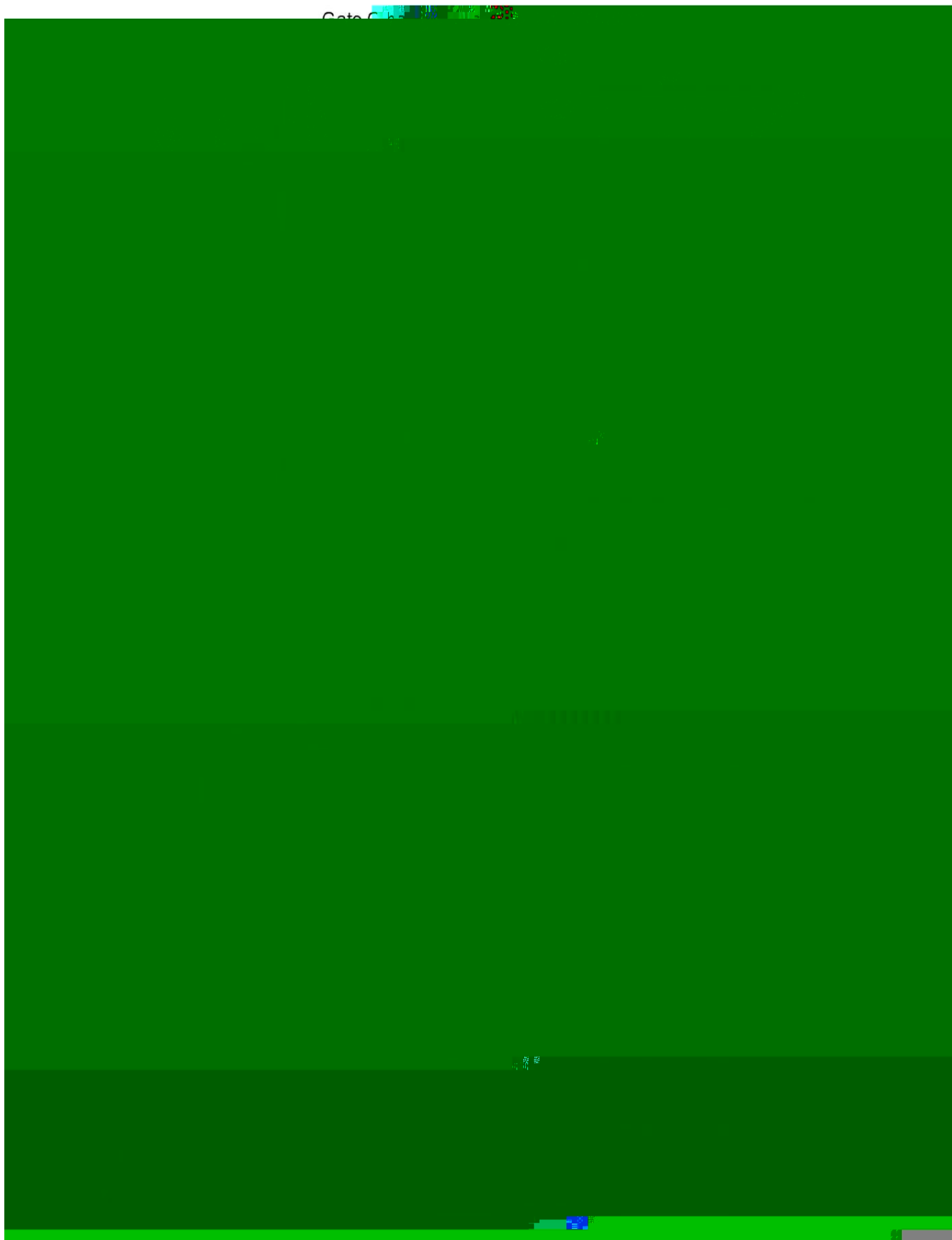
Input Capacitance	$C_{iss}$	-	6820	-	pF	$V_{GS}=0V, V_{DS}=25V,$ $f=1MHz$
Output Capacitance	$C_{oss}$	-	632	-		
Reverse Transfer Capacitance	$C_{rss}$	-	20	-		
Gate Total Charge	$Q_g$	-	75	-	nC	$V_{GS}=10V, V_{DS}=240V,$ $I_D=59A$
Gate-Source charge	$Q_{gs}$	-	20	-		
Gate-Drain charge	$Q_{gd}$	-	37	-		
Turn-on delay time	$t_{d(on)}$	-	145	-	ns	$V_{DD}=150V, I_D=59A,$ $R_G=25$
Rise time	$t_r$	-	670	-		
Turn-off delay time	$t_{d(off)}$	-	125	-		
Fall time	$t_f$	-	210	-		
Gate resistance	$R_G$	-	400	-	m	$V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$

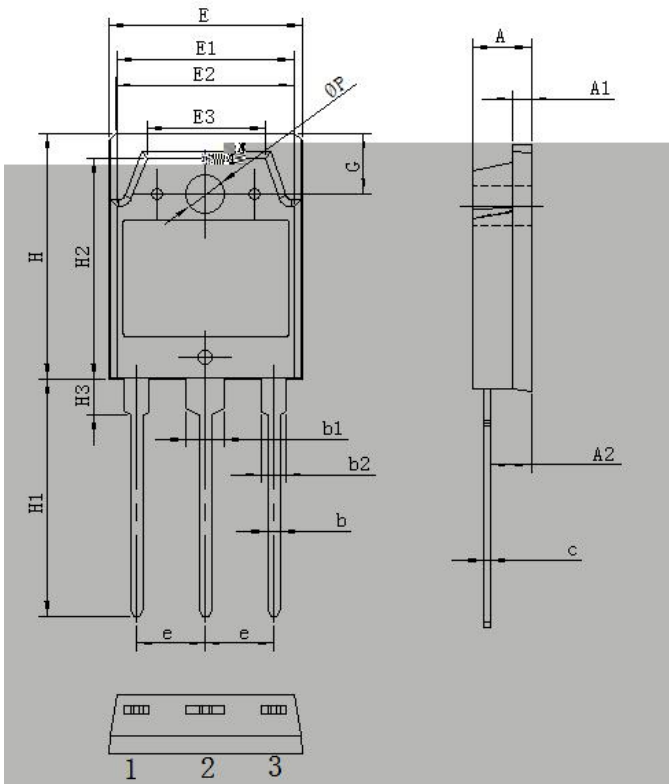
Body Diode Forward Voltage	$V_{SD}$	-	-	1.4	V	$V_{GS}=0V, I_{BS}=59A$
Body Diode Continuous Forward Current	$I_S$	-	-	59	A	$T_C=25^\circ C$
Body Diode Reverse Recovery Time	$t_{rr}$	-	245	-	ns	$T_C=25^\circ C, I_S=59A, di/dt=100A/us$
Body Diode Reverse Recovery Charge	$Q_{rr}$	-	6.7	-	$\mu C$	











Symbol	单位 mm		
	Min	Nom	Max
A	4.60	4.80	5.00
A1	1.3	1.5	1.7
A2	1.20	1.40	1.60
b	0.80	1.0	1.20
b1	2.90	3.10	3.30
b2	1.90	2.10	2.30
c	0.50	0.60	0.70
e	5.25	5.45	5.65
E	15.2	15.6	16.0
E1	13.2	13.4	13.6
E2	13.1	13.3	13.5
E3	9.1	9.3	9.5
H	19.8	20.0	20.2
H1	20.1	20.3	20.5
H2	18.5	18.7	18.9
H3	3.2	3.5	3.8
G	4.8	5.0	5.2
ΦP	3.00	3.20	3.40